

F12 – Output Stages

Outline

- Classification of output stages
 - Class A
 - Class B
 - Class AB
 - Class C
 - Class D
- Operation and power efficiency of class A, B, and AB
- CMOS implementation of class AB output stage
- Power transistors

Reading Guide

Sedra/Smith 7ed int

- Chapter 11.1-5 (output stages)
- (Chapter 11.6 (variations))
- Chapter 11.7 (CMOS AB stage)
- (Chapter 11.8-10 (PAs, power devices))

Problems

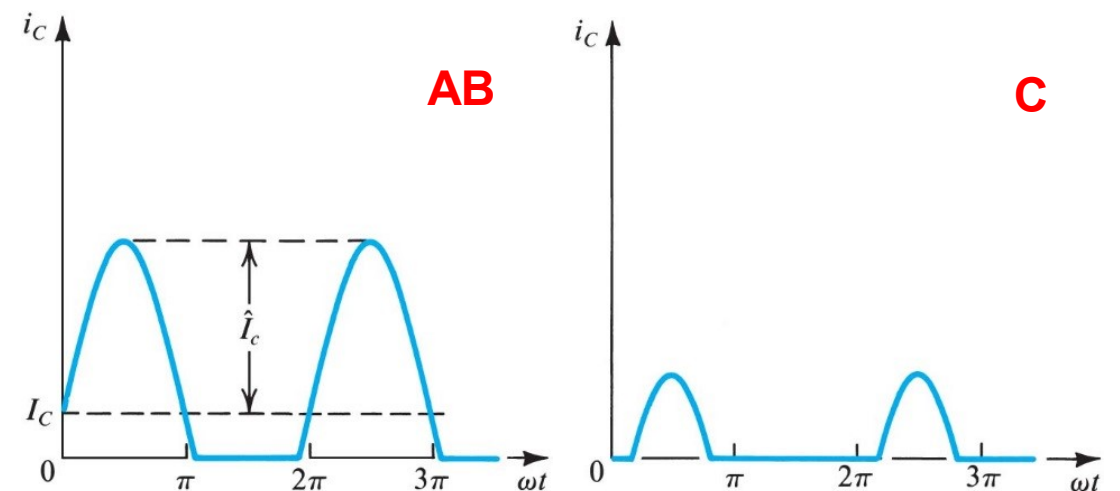
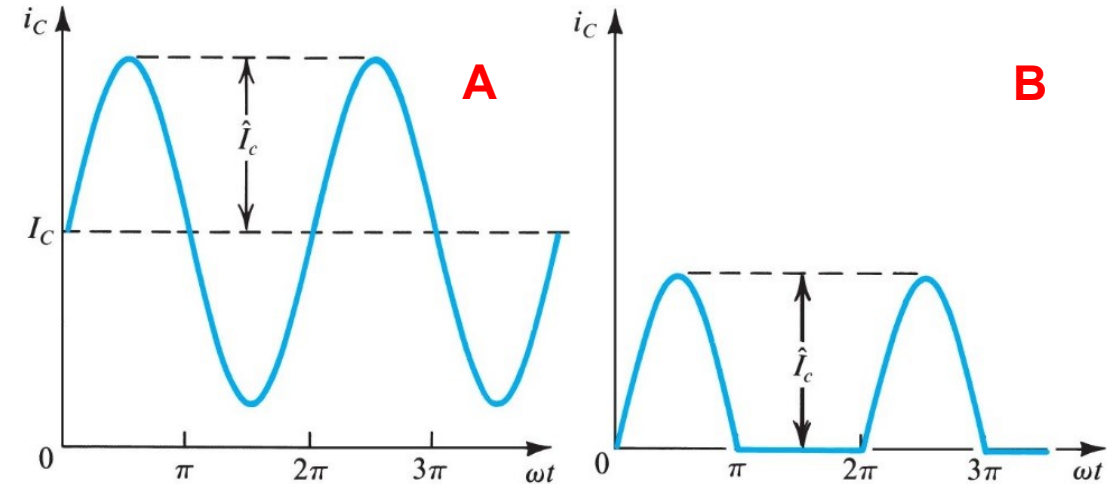
Sedra/Smith 7ed int

- P11.2, 11.11, 11.19(a-b), 11.56



Classification of Output Stages

- Output stages are primarily classified by their periodic active angle, θ
- Linear and “quasi-linear complementary” amplifiers
 - Class A: $\theta = 360^\circ$
 - Class B: $\theta = 180^\circ$
 - Class AB: $180^\circ < \theta \ll 360^\circ$
- Small angle (tuned resonator) amplifiers
 - Class C: $0^\circ < \theta < 180^\circ$
- Pulse width modulated (switching) amplifiers
 - Class D: $\theta = 360^\circ$ non-linear
- ... and more sophisticated classes (E, F, G, H, etc.)



Source(/ Emitter) Follower as an Output Stage

- Common drain(/ collector) a.k.a. source(/ emitter) follower

- High input resistance

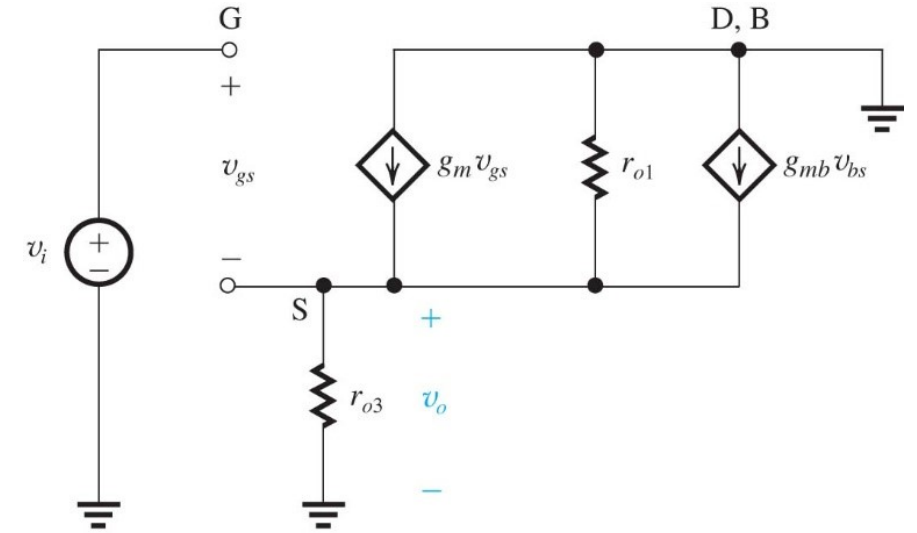
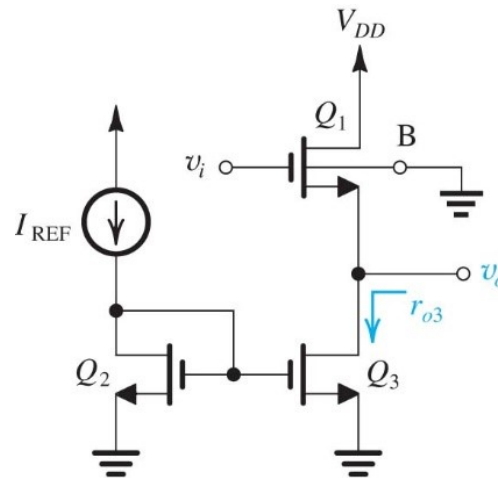
$$R_i = \infty$$

- Voltage buffer

$$A_{vo} \approx \frac{1}{1 + \chi}$$

- Low output resistance

$$R_o \approx \frac{1}{g_m(1 + \chi)}$$



Ideal input/ output resistance for a voltage amplifier, but gain must be provided by previous stages.

Class A

- Common drain(/ emitter), Q1, with active load, Q2
- Balanced supplies ($\pm V_{CC}$) allow load to ground

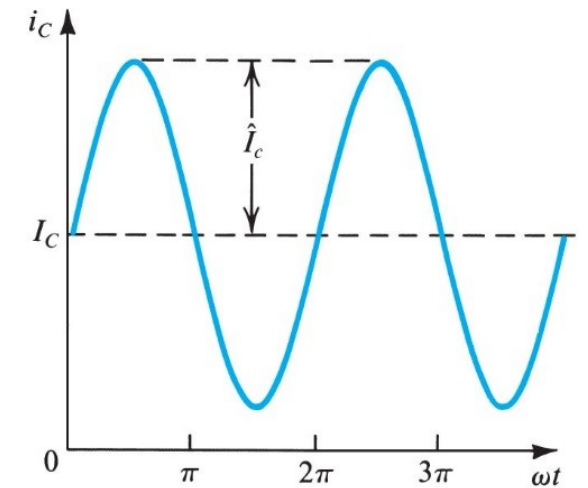
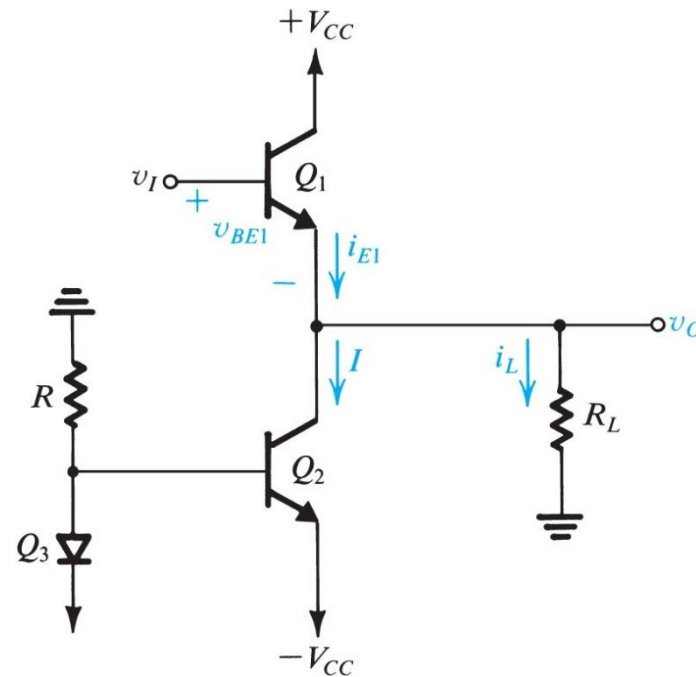
$$V_{EE} = -V_{CC}$$

- Bias/ load should be designed to support rail-to-rail signal operation
 - Positive output: Q1 on
 - Negative output: Q1 off

$$v_O = -IR_L \leq -V_{CC}$$

\Leftrightarrow

$$R_L \geq \frac{V_{CC}}{I}$$





Class A: Large Signal Operation

- Non-inverting operation centred on $i_{E1} = I$ and $v_O = 0$
 - Rail-to-rail operation (neglecting Q1 and Q2 v_{CEsat})

$$R_L \geq \frac{V_{CC}}{I} \Rightarrow -V_{CC} < v_O < V_{CC}$$

- High output (Q1 on)

$$v_O = V_{CC}, \quad i_{E1} = 2I$$

$$\Leftrightarrow$$

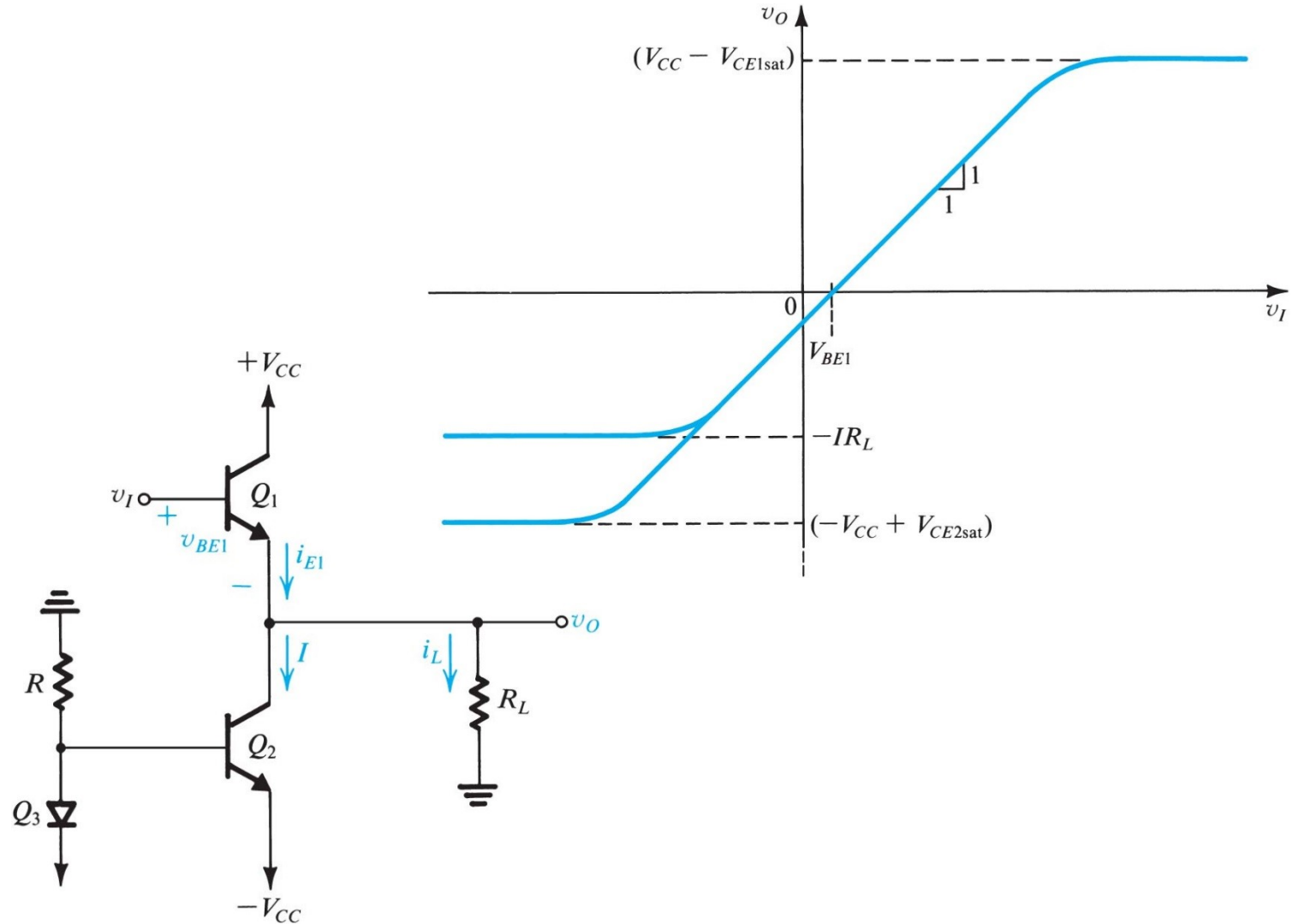
$$i_L = i_{E1} - I = I$$

- Low output (Q1 off)

$$v_O = -V_{CC}, \quad i_{E1} = 0$$

$$\Leftrightarrow$$

$$i_L = i_{E1} - I = -I$$



Class A: Signal Waveforms

- Rail-to-rail output voltage swing (neglecting v_{CEsat})
 - Load resistance selected to support rail-to-rail operation

$$R_L = \frac{V_{CC}}{I}$$

- Collector-emitter voltage shifted and inverted w.r.t output

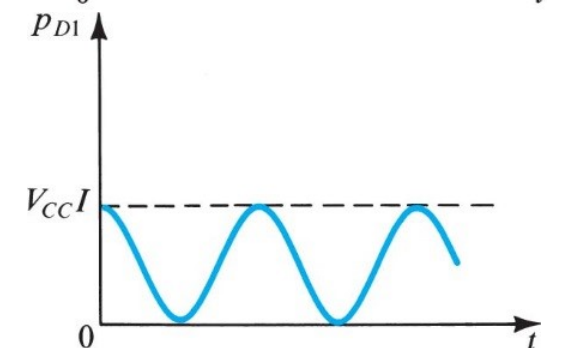
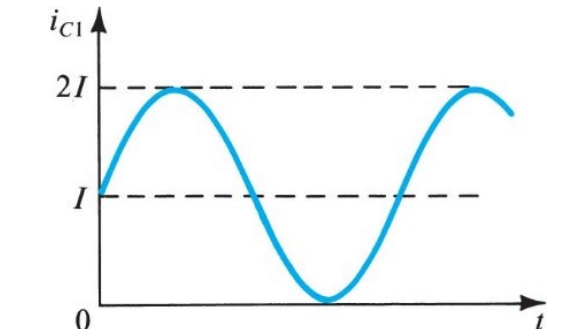
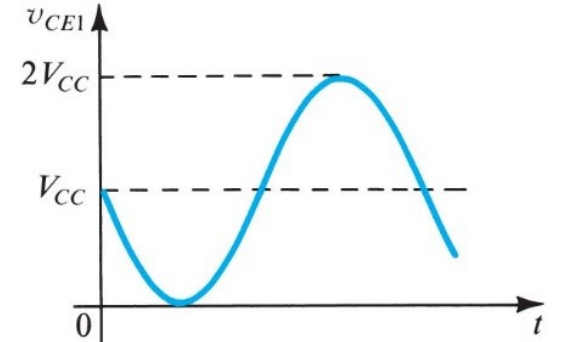
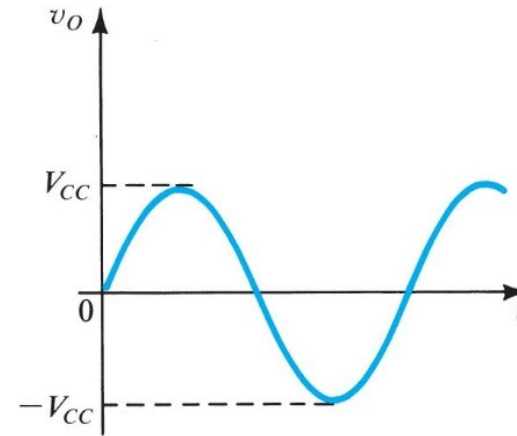
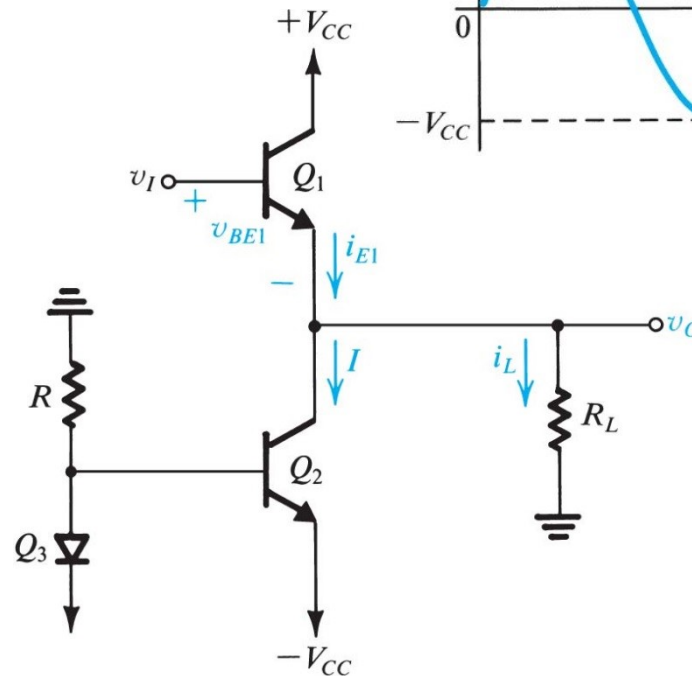
$$-V_{CC} < v_{CE1} = V_{CC} - v_O < V_{CC}$$

- Current swing

$$0 < i_{C1} \approx I + v_O R_L < 2I$$

- Power dissipated in Q1

$$0 < p_{D1} = v_{CE1} i_{C1} < V_{CC} I$$





Class A: Power Efficiency

- Power efficiency
 - Ratio of load power, P_L , to supply power, P_S

$$\eta = \frac{P_L}{P_S} = \frac{1}{4} \left(\frac{\hat{V}_o}{IR_L} \right) \left(\frac{\hat{V}_o}{V_{CC}} \right) \leq 25\%$$

$$10\% < \eta_{\text{typical}} < 20\%$$

- Harmonic output assumed

$$v_o = \hat{V}_o \sin(\omega t) = \hat{V}_o \sin\left(\frac{2\pi}{T} t\right)$$

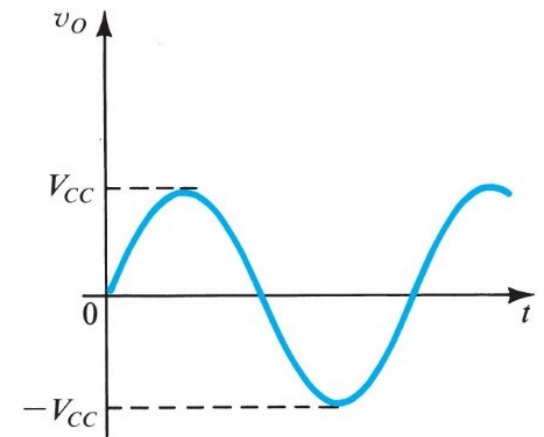
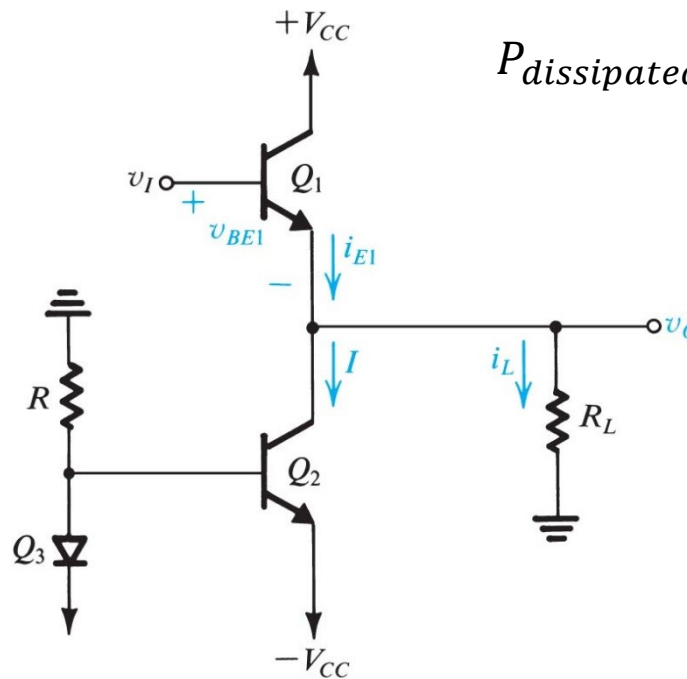
- Load power

$$P_L = \frac{v_o^2}{R_L} = \frac{1}{2} \frac{\hat{V}_o^2}{R_L}$$

- Supply power

$$P_S = P_{S+} + P_{S-} = 2V_{CC}I$$

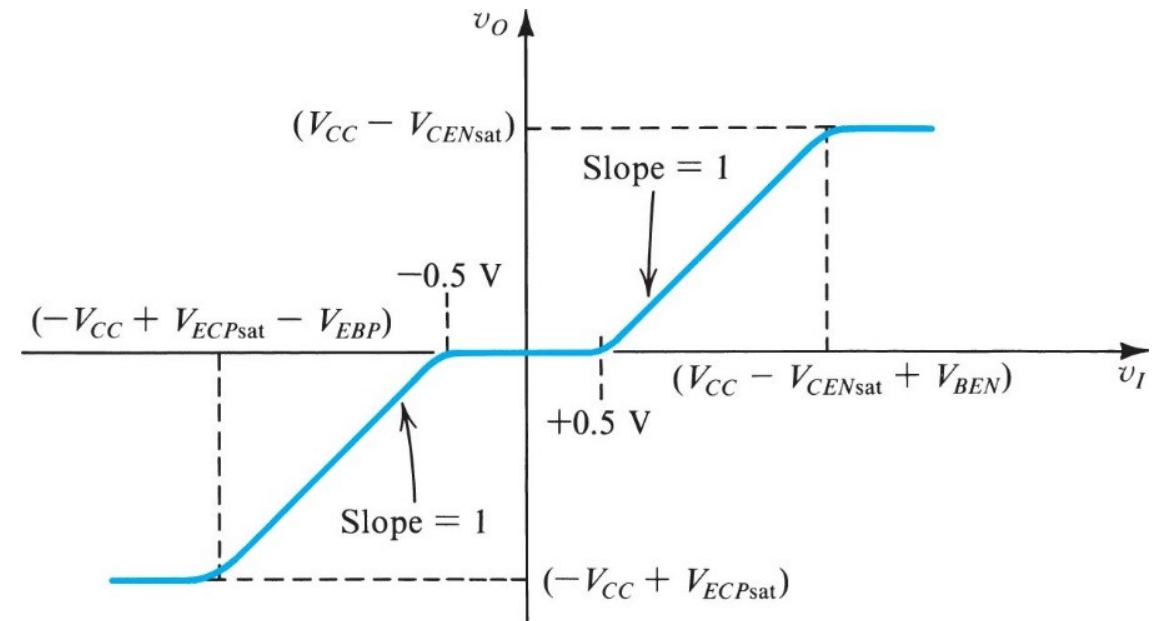
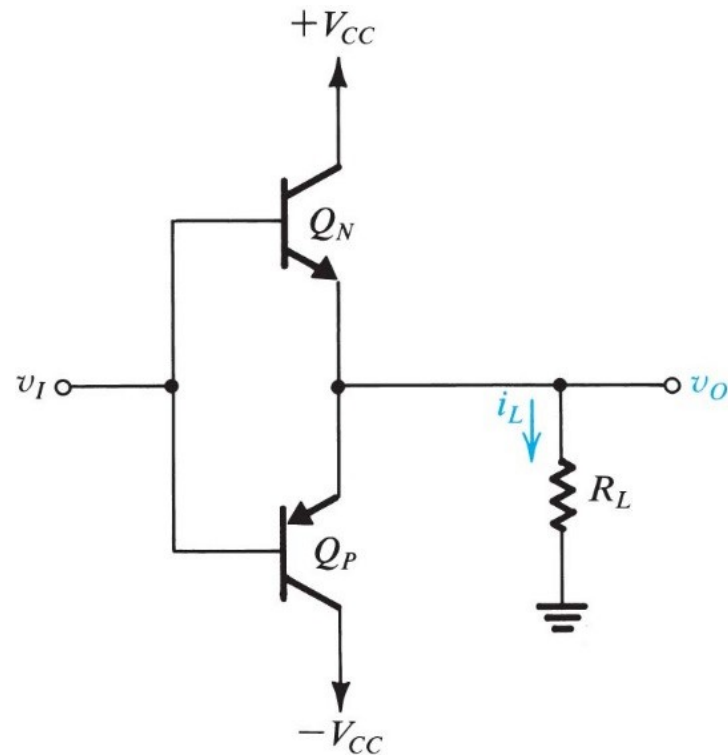
$$P_{\text{dissipated}} = P_L - P_S = 2V_{CC}I - \frac{1}{2} \frac{\hat{V}_o^2}{R_L}$$



Power dissipation monotonically reduced with output voltage level, but high quiescent value and low maximum efficiency.

Complementary Emitter(/ Source) Follower as an Output Stage

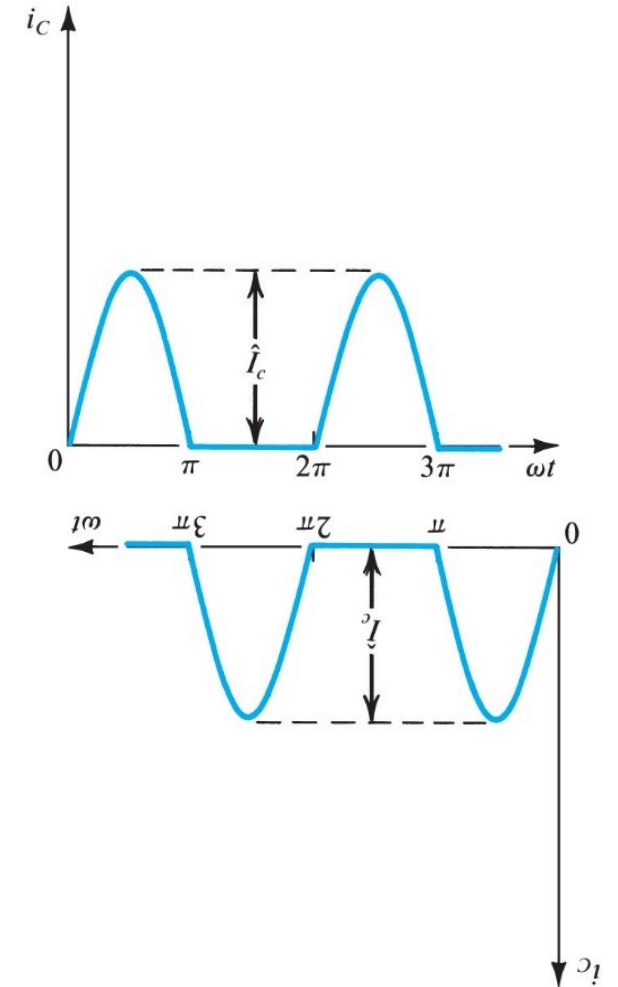
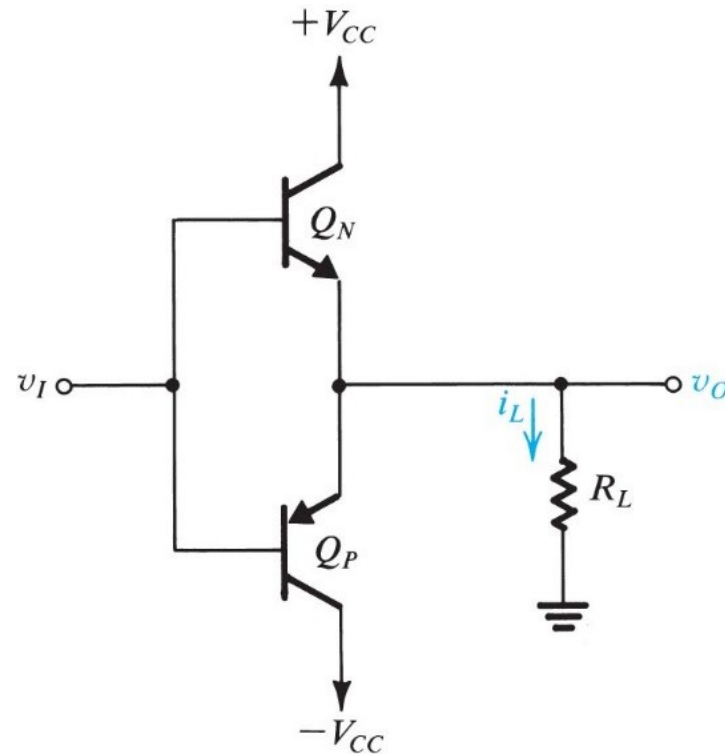
- Complementary push-pull configuration
 - One transistor active
 - One transistor cutoff



**Q1 sources (pushes) load current,
Q2 sinks (pulls) load current.**

Class B

- Complementary push-pull configuration
- Balanced supplies ($\pm V_{CC}$) allow load to ground
- Supports rail-to-rail operation (within v_{CEsat})
 - Positive output: QN on, QP off
 - Negative output: QP on, QN off
- Dead band about zero input
 - Both QN and QP cutoff

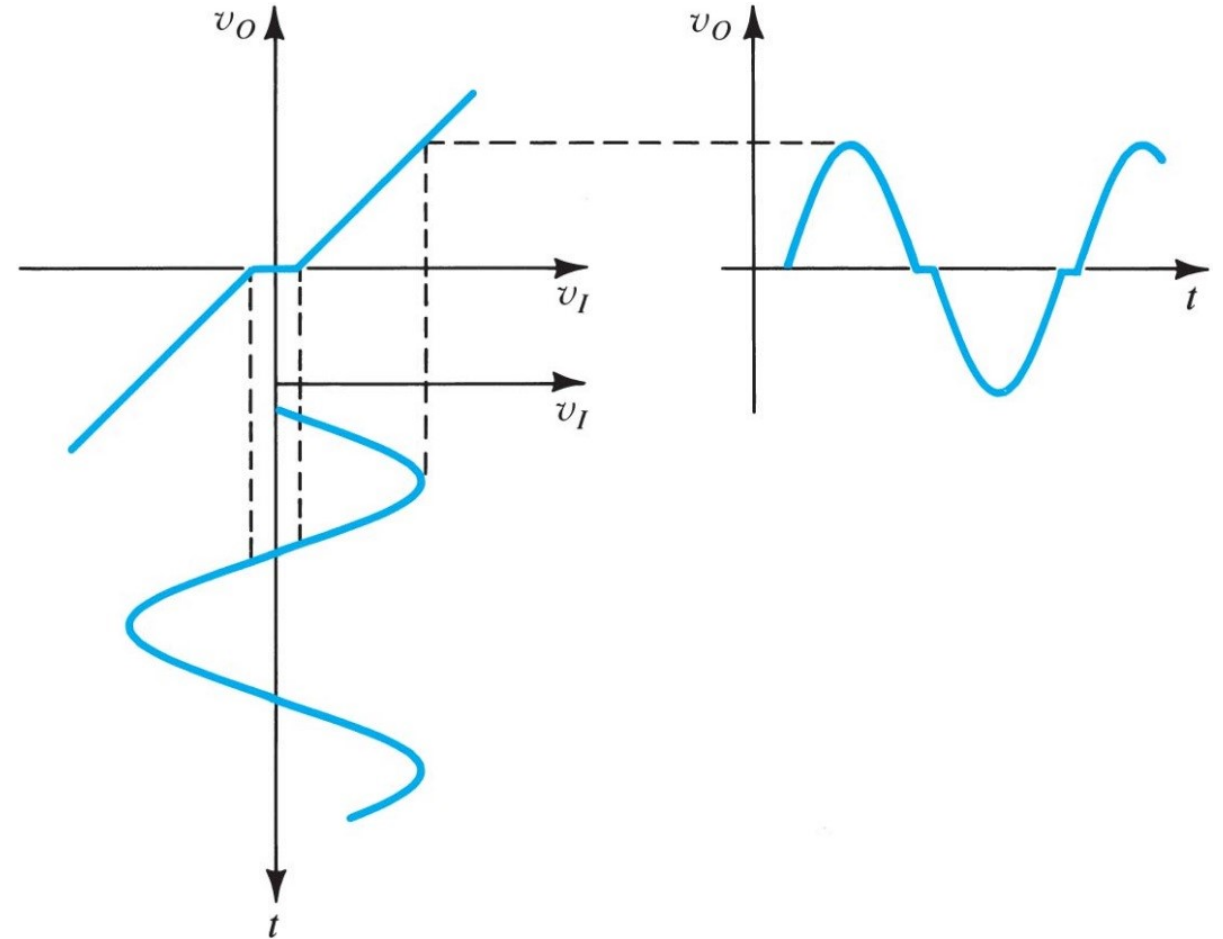
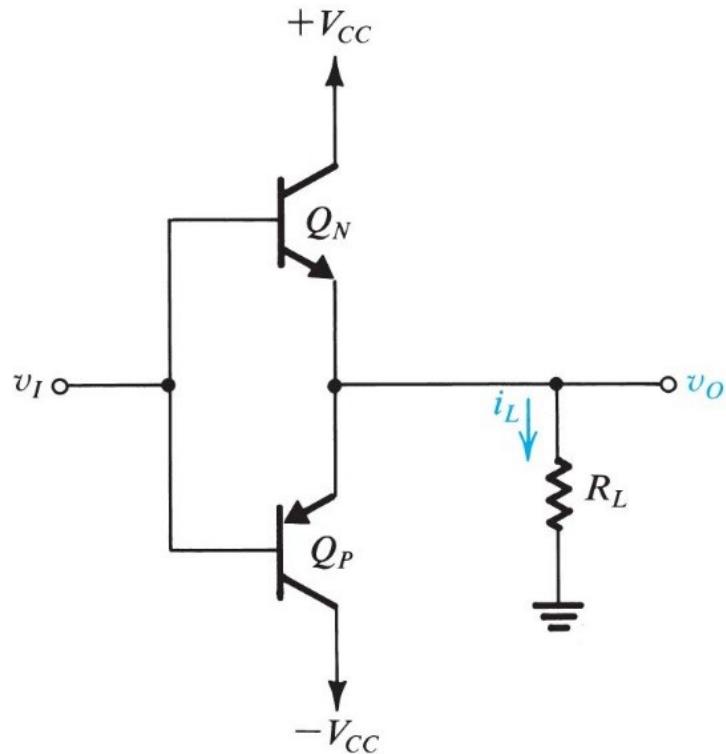


Class B: Crossover Distortion

- Dead band due to conduction threshold voltage

$$|v_I| < v_{BE\text{active}} \Rightarrow v_O \approx 0$$

- Signal distortion at zero-crossing



Crossover distortion can be circumvented through use of clever biasing.



Class B: Power Efficiency

- Power efficiency
 - Ratio of load power, P_L , to supply power, P_S

$$\eta = \frac{P_L}{P_S} = \frac{\pi}{4} \left(\frac{\hat{V}_o}{V_{CC}} \right) \leq 78.5\%$$

$$40\% < \eta_{\text{typical}} < 60\%$$

- Harmonic output assumed

$$v_o = \hat{V}_o \sin(\omega t) = \hat{V}_o \sin\left(\frac{2\pi}{T} t\right)$$

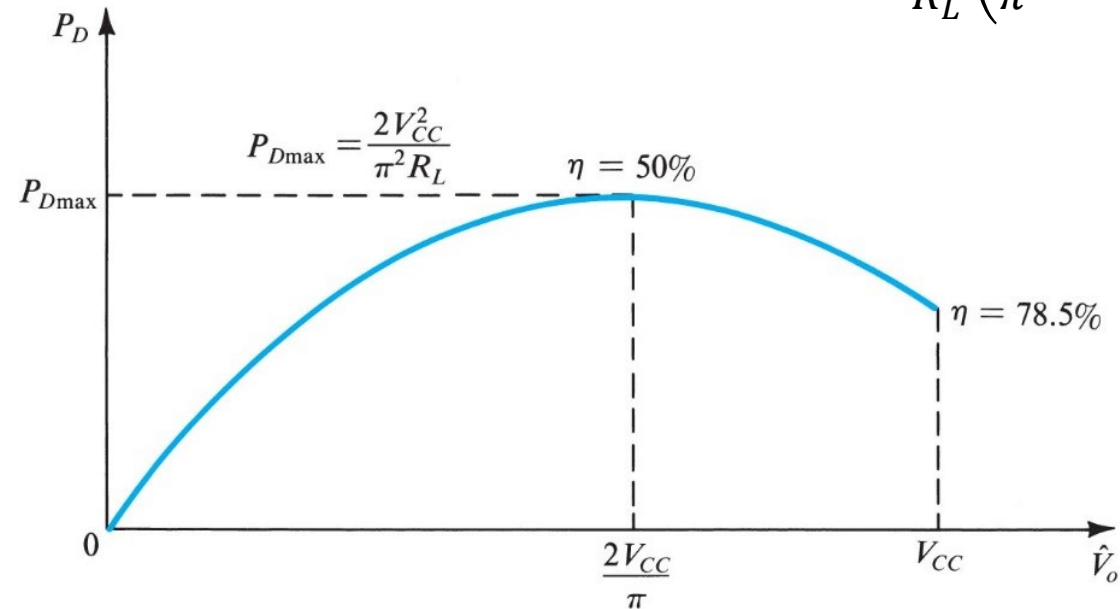
- Load power

$$P_L = \frac{v_o^2}{R_L} = \frac{1}{2} \frac{\hat{V}_o^2}{R_L}$$

- Supply power

$$P_S = P_{S+} + P_{S-} = \frac{2}{\pi} \frac{\hat{V}_o}{R_L} V_{CC}$$

$$P_D = P_{\text{dissipated}} = P_L - P_S = \frac{\hat{V}_o}{R_L} \left(\frac{2}{\pi} V_{CC} - \frac{1}{2} \hat{V}_o \right)$$



Power dissipation low for low and high output voltage, and quite good maximum efficiency.

Class B: Single Supply

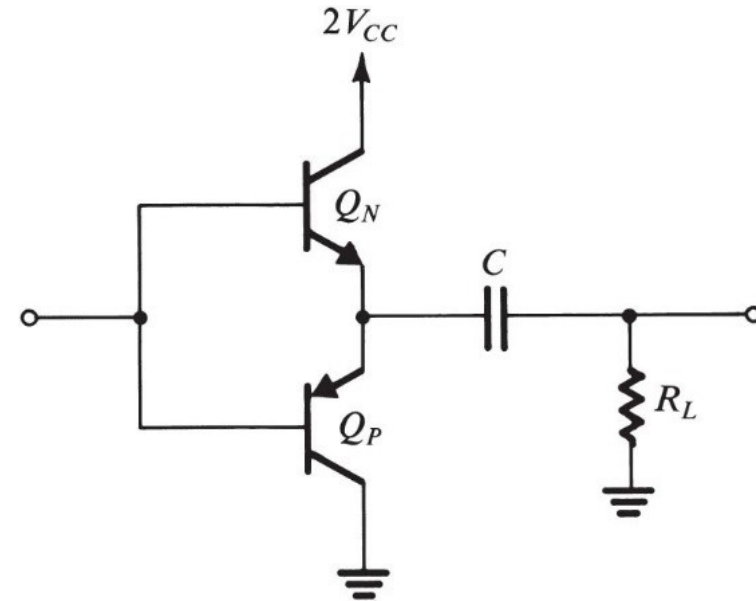
- Shifted positive supply

$$V'_{CC} = V_{CC} + V_{EE} = \{V_{EE} = V_{CC}\} = 2V_{CC}$$

- Grounded current sink

$$V'_{EE} = -V_{EE} + V_{EE} = 0$$

- Capacitively coupled load to ground
 - Separates dc from signal



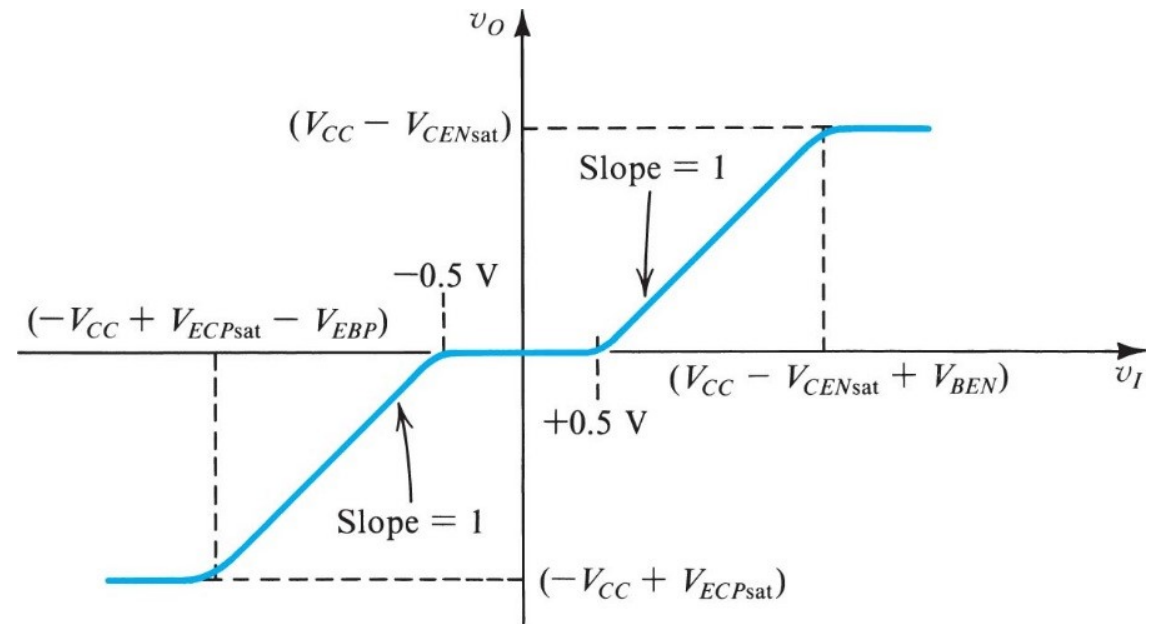
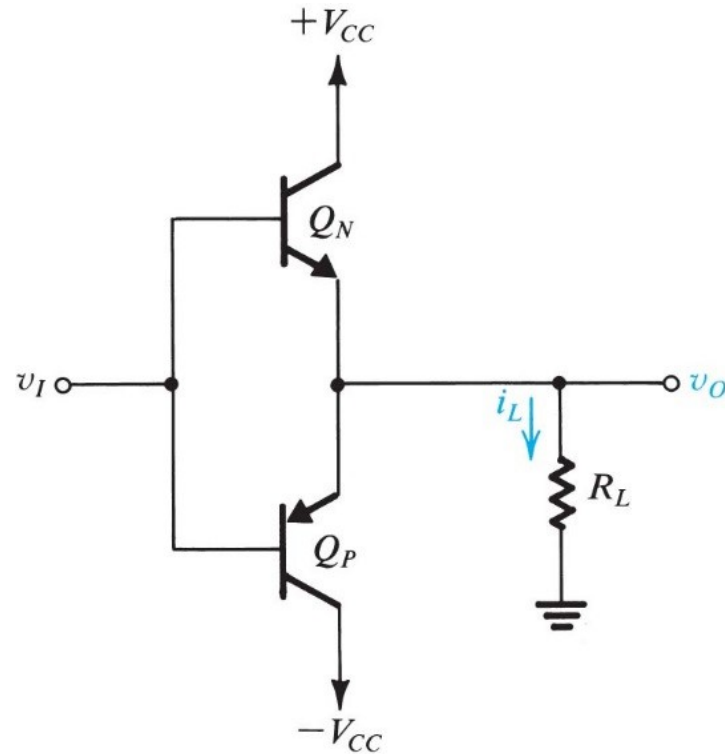
BREAK



Attractive to eliminate class B conduction threshold; why and how?

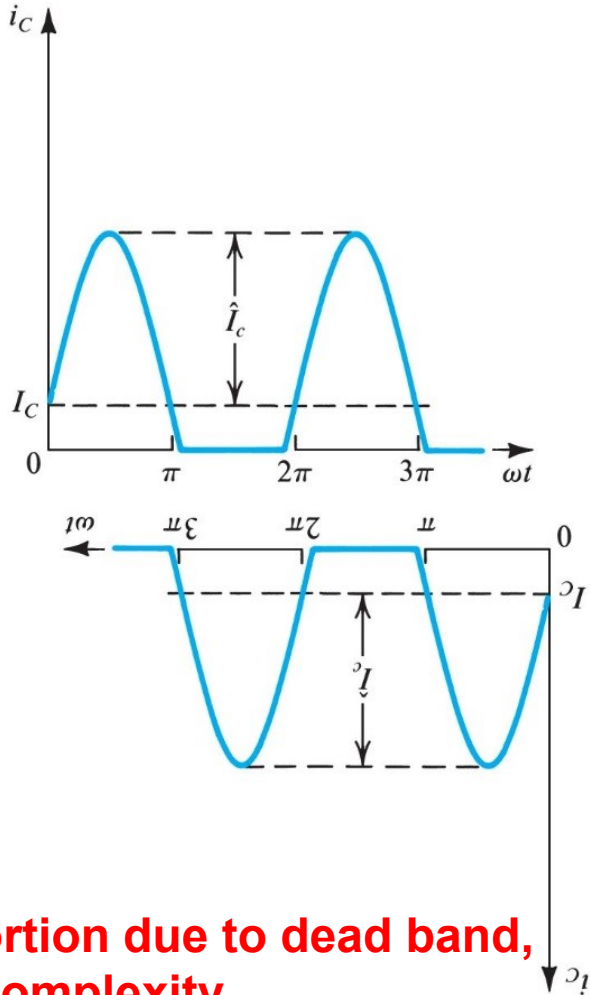
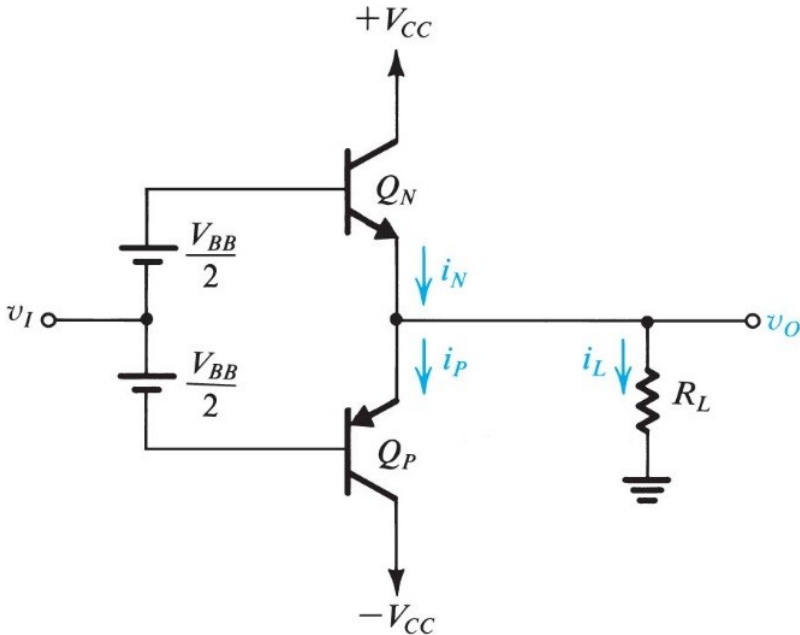
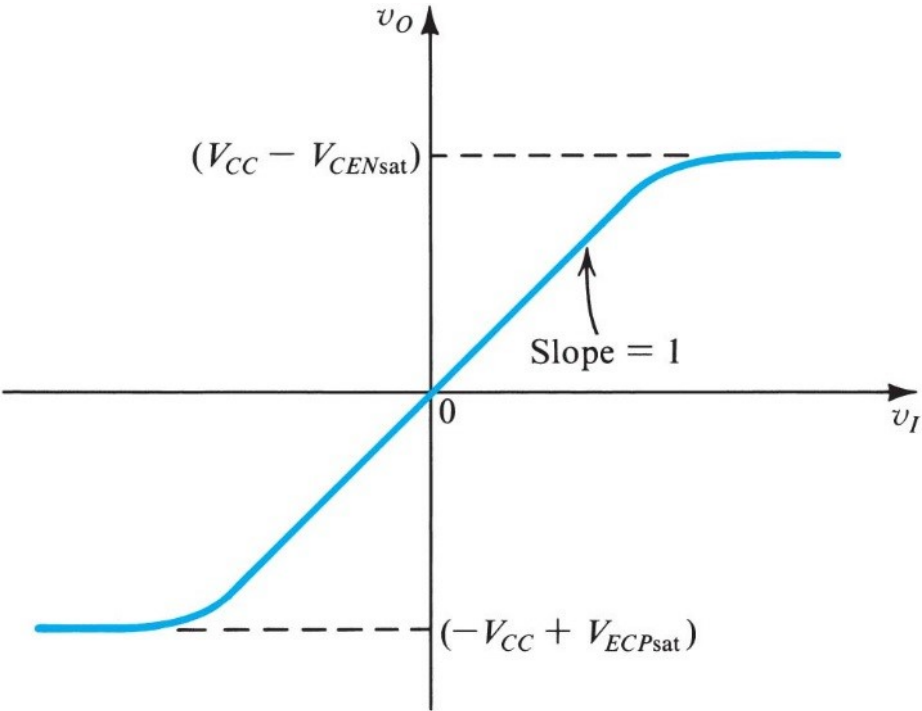


Think, think, think.



Class AB

- Class A at very low bias, or bias on a class B stage
 - Removes conduction threshold, no crossover distortion
 - Small quiescent power dissipation



Elimination of harmonic distortion due to dead band, at the cost of efficiency and complexity.

Class AB: Quiescent Current and Large Signal Operation

- Input bias generates quiescent current

$$i_N \Big|_{v_O=0} = i_P \Big|_{v_O=0} = I_Q = I_S \exp\left(\frac{V_{BB}}{2V_T}\right)$$

- Positive output voltage (negative just opposite)

- Output follows input

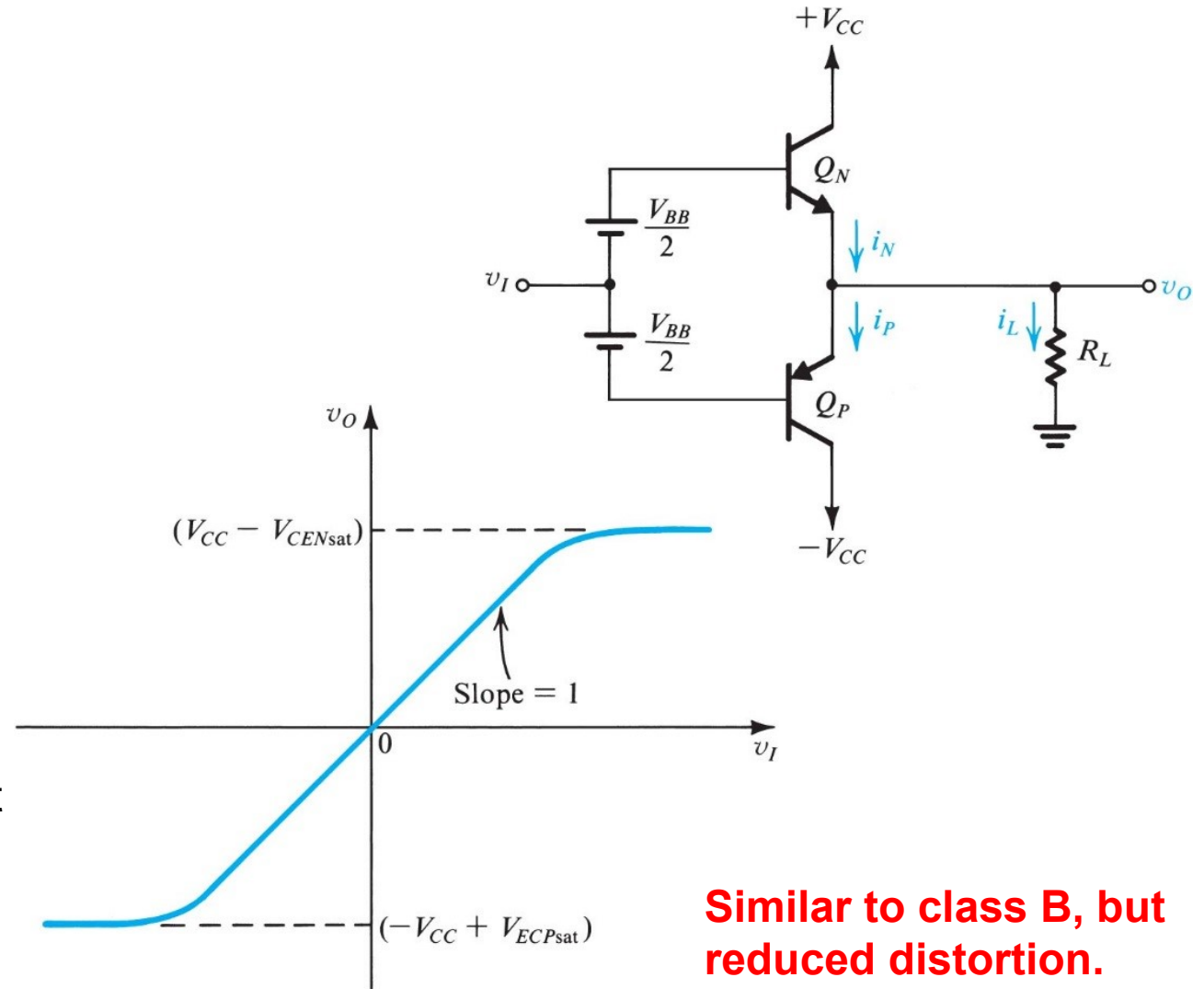
$$v_O = v_I + \frac{V_{BB}}{2} - v_{BEN}, \quad i_L = \frac{v_O}{R_L}$$

- Incremental load current supplied by QN, which requires increased QN base drive

$$i_N = i_P + i_L, \quad v_{BEN} + v_{EBP} = V_{BB}$$

- Product of device currents remain constant

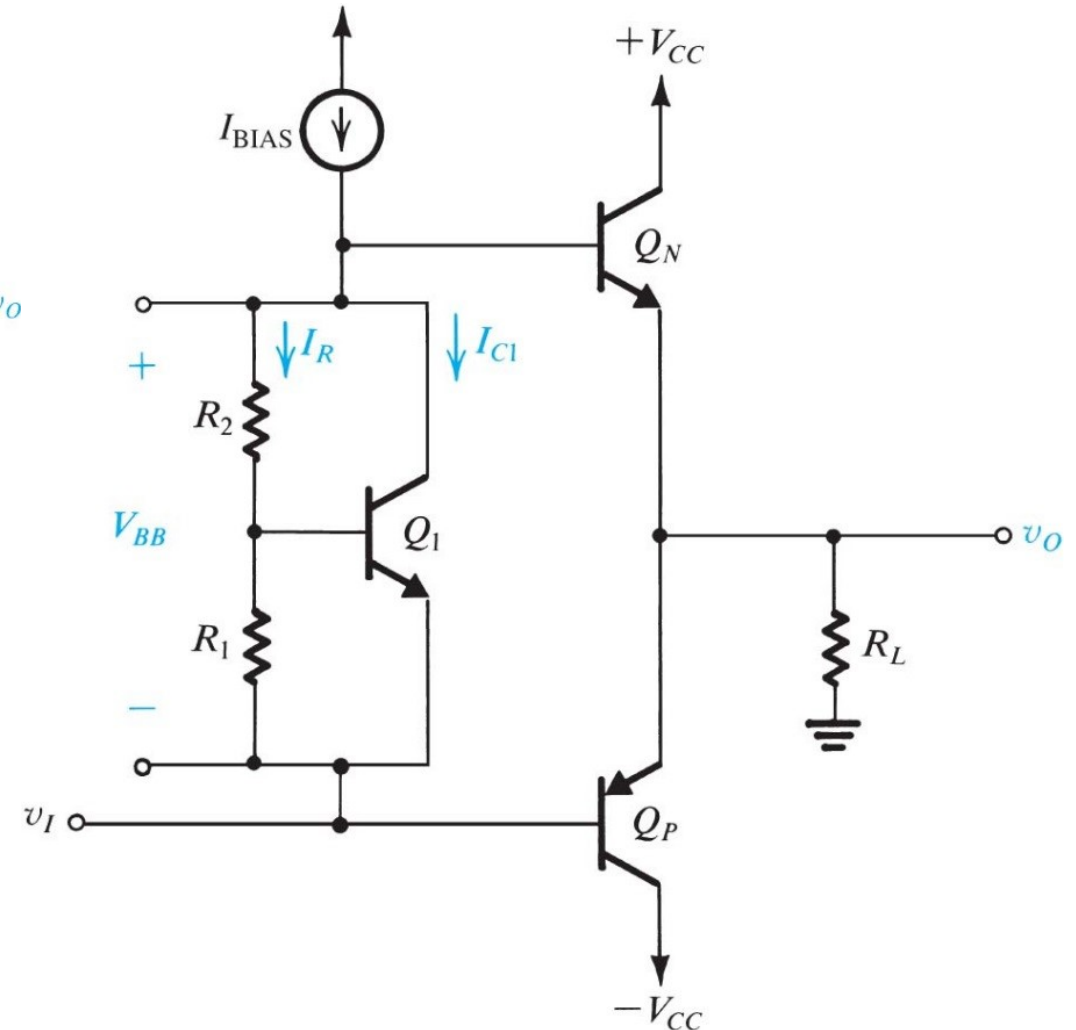
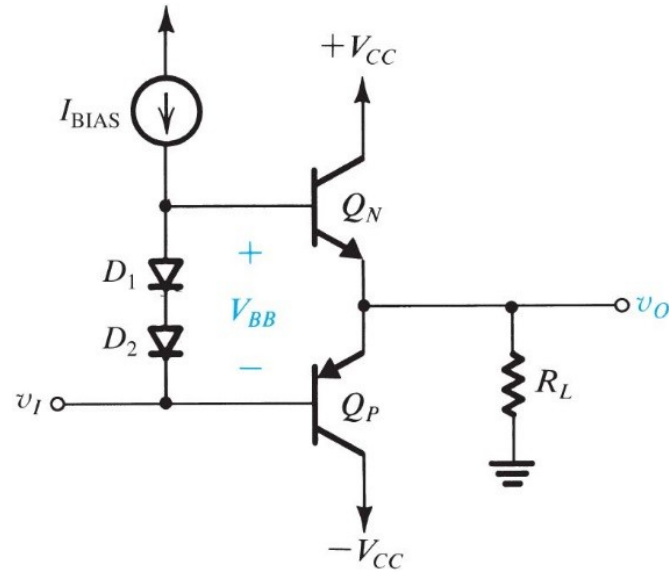
$$i_N i_P = I_Q^2 \Rightarrow i_N^2 - i_L i_N - I_Q^2 = 0$$



Similar to class B, but reduced distortion.

Biassing the BJT Class AB Input

- Diodes
 - Simple but primitive
- Base-emitter multiplier
 - Design ratio using resistances

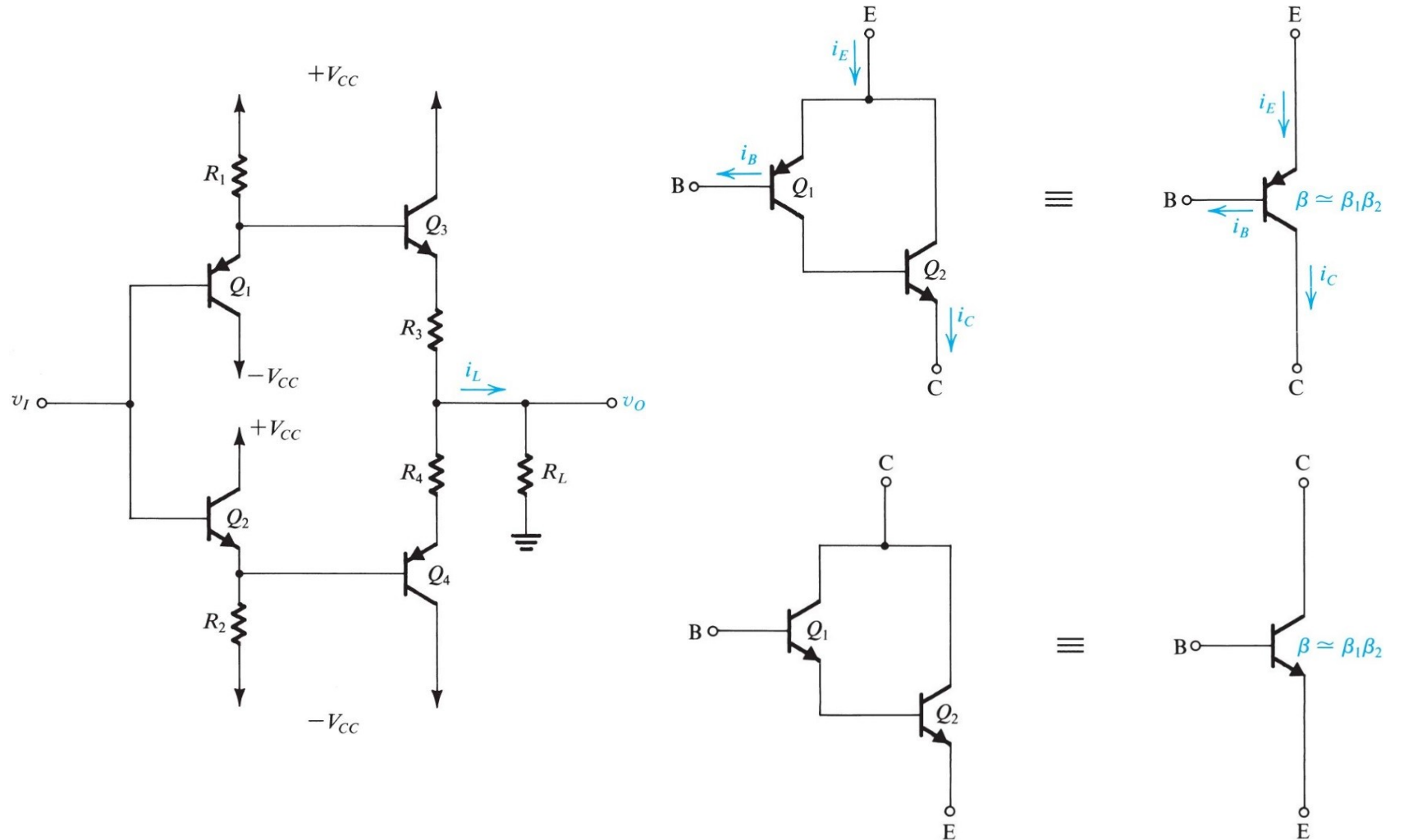


$$I_R = \frac{V_{BE1}}{R_1}$$

$$V_{BB} = I_R(R_1 + R_2) = V_{BE1} \left(1 + \frac{R_2}{R_1} \right)$$

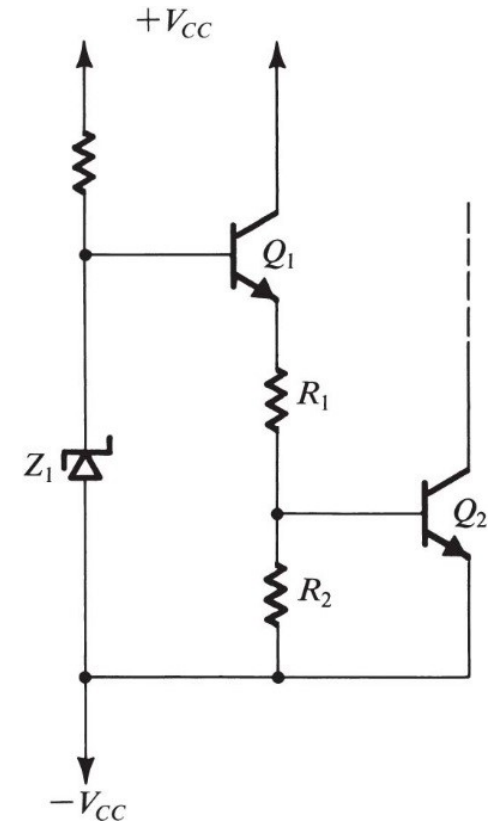
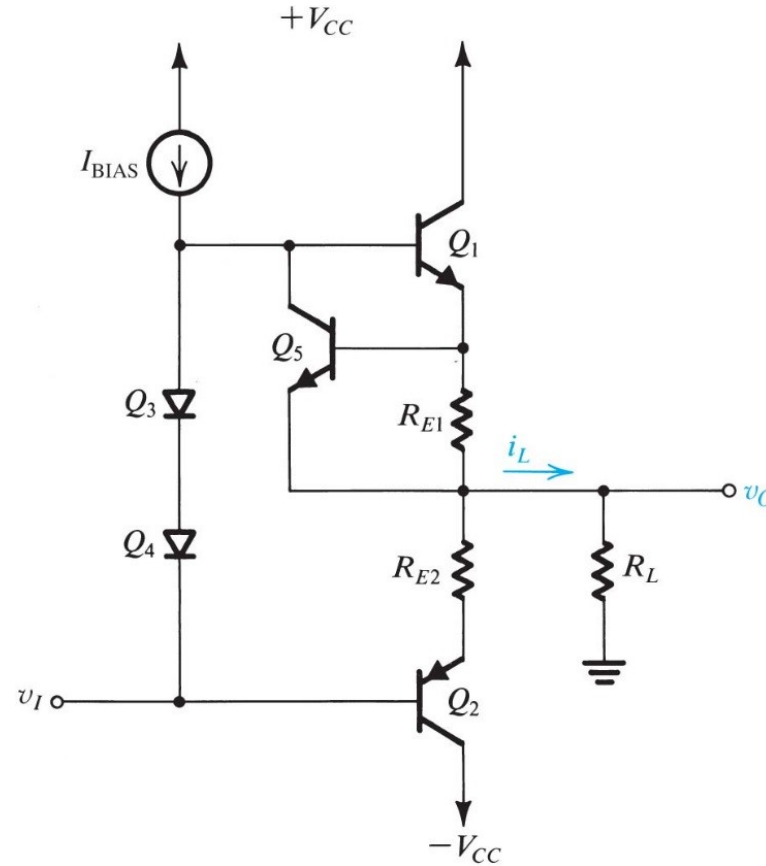
(Class AB: BJT Variations)

- Input emitter followers
 - Buffers input signal
 - Provides AB biasing
- Compound devices boost performance
 - Darlington configuration
 - Compound PNP



(Protection Circuits)

- Output short circuit protection, protects against too high load current
 - Q5 normally off
 - High current in R_{E1} turns Q5 on
 - Q5 on turns Q1 off
- Thermal shutdown, protects chip against meltdown
 - Q2 normally off
 - Z1 positive temperature coefficient
 - Q1 negative temperature coefficient
 - High temp turns Q2 on
 - Q2 on robs bias from another stage



Protect the amplifier from the user.



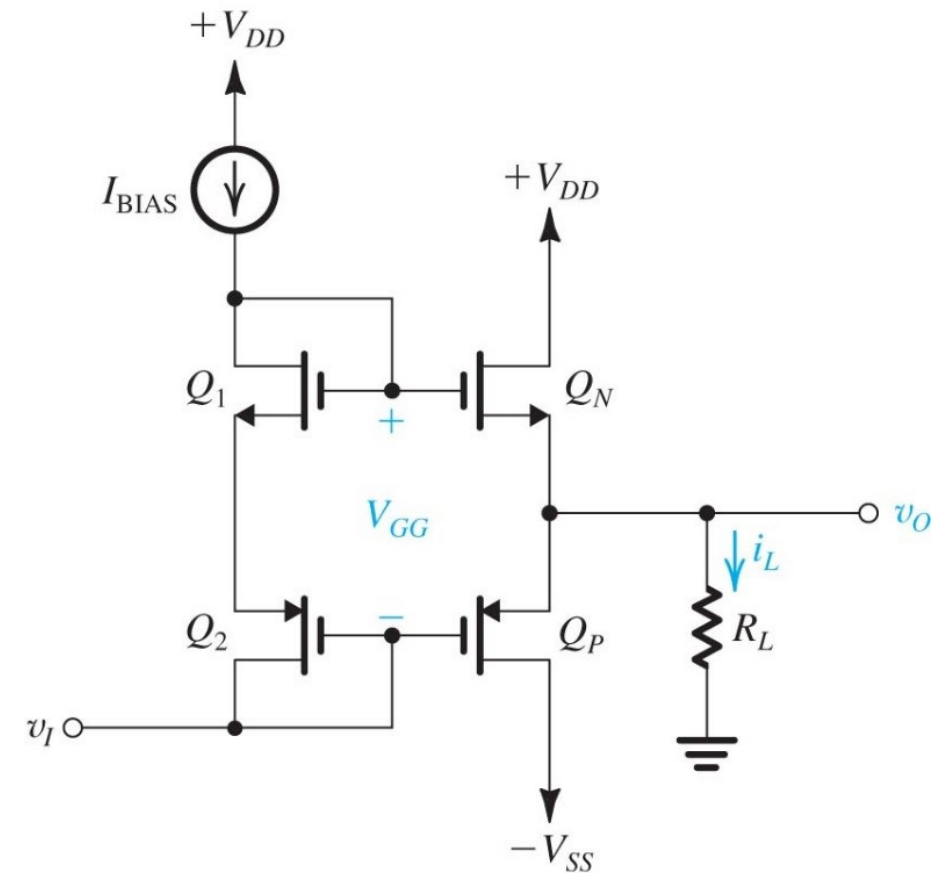
Class AB: Classical CMOS Configuration

- Complementary source follower with diode connected input devices
 - Equivalent to BJT AB with diode bias
 - Voltage buffer
 - Low output resistance
 - Limits to the output swing
 - QN and QP overdrive voltages
 - Input circuit active load overdrive voltage
 - Bias current source overdrive voltage

$$-V_{SS} + V_{OVI} + |V_{tp}| + |v_{OVP}| < v_O < V_{DD} - V_{OVN} - V_{tn} - v_{OVN}$$

- Quiescent current due to input bias

$$i_{DN}\Big|_{v_O=0} = i_{DP}\Big|_{v_O=0} = I_Q = I_{BIAS} \frac{(W/L)_n}{(W/L)_1}$$



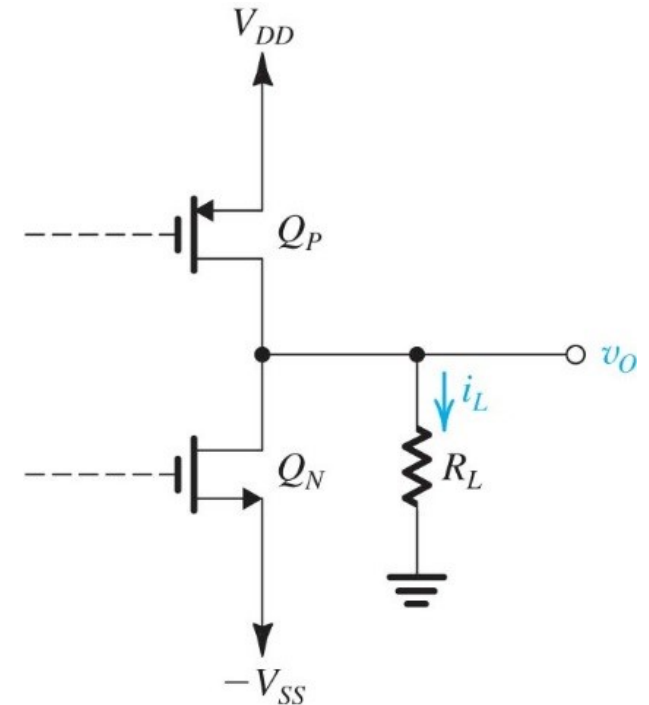
Class AB: Wide Swing CMOS Configuration

- Complementary push-pull common source
 - Provides high voltage gain, as compared to follower
 - Moderately high output impedance

$$R_o = r_{on} || r_{op}$$

- Output swing improved to within an overdrive voltage from the supplies

$$-V_{SS} + v_{OVN} < v_o < V_{DD} - v_{OVP}$$



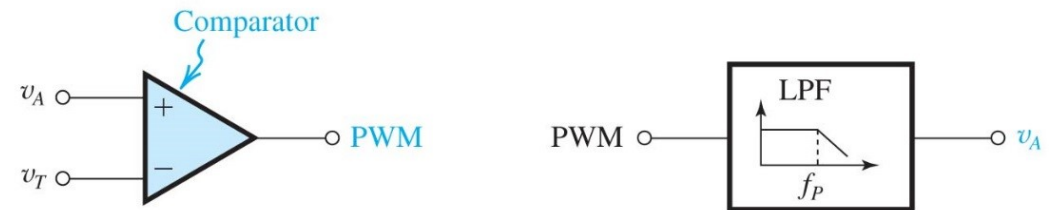
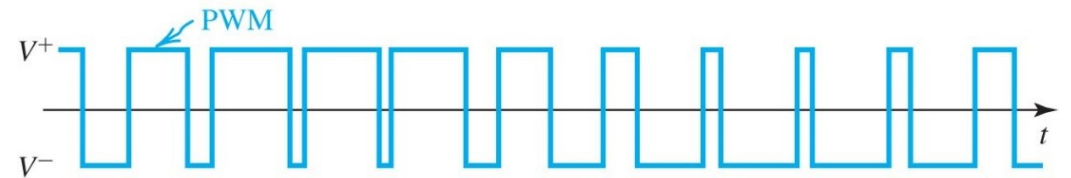
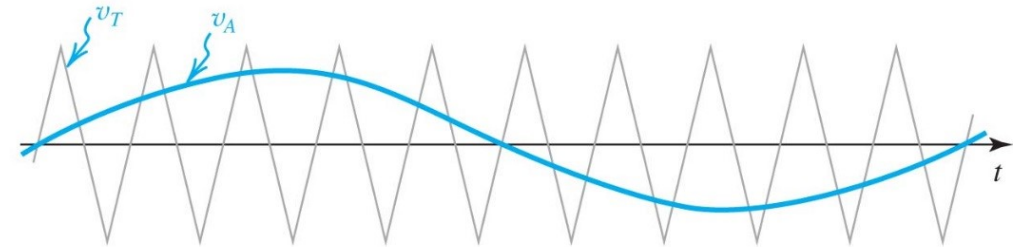
Output resistance can be improved by feedback.

Class D: High Efficiency Switching Amplifier

- High efficiency (ideally 100%)
 - Rapid switch between on and off yields only device power dissipation in a brief moment
 - On or off, no simultaneous voltage and current

$$P_L = v_L i_L \approx V_S I_S = P_S$$

- Transmitter
 - Pulse width modulation (PWM) of signal at a high frequency w.r.t. signal frequency
- Receiver
 - Demodulation by low-pass filtering (moving average)

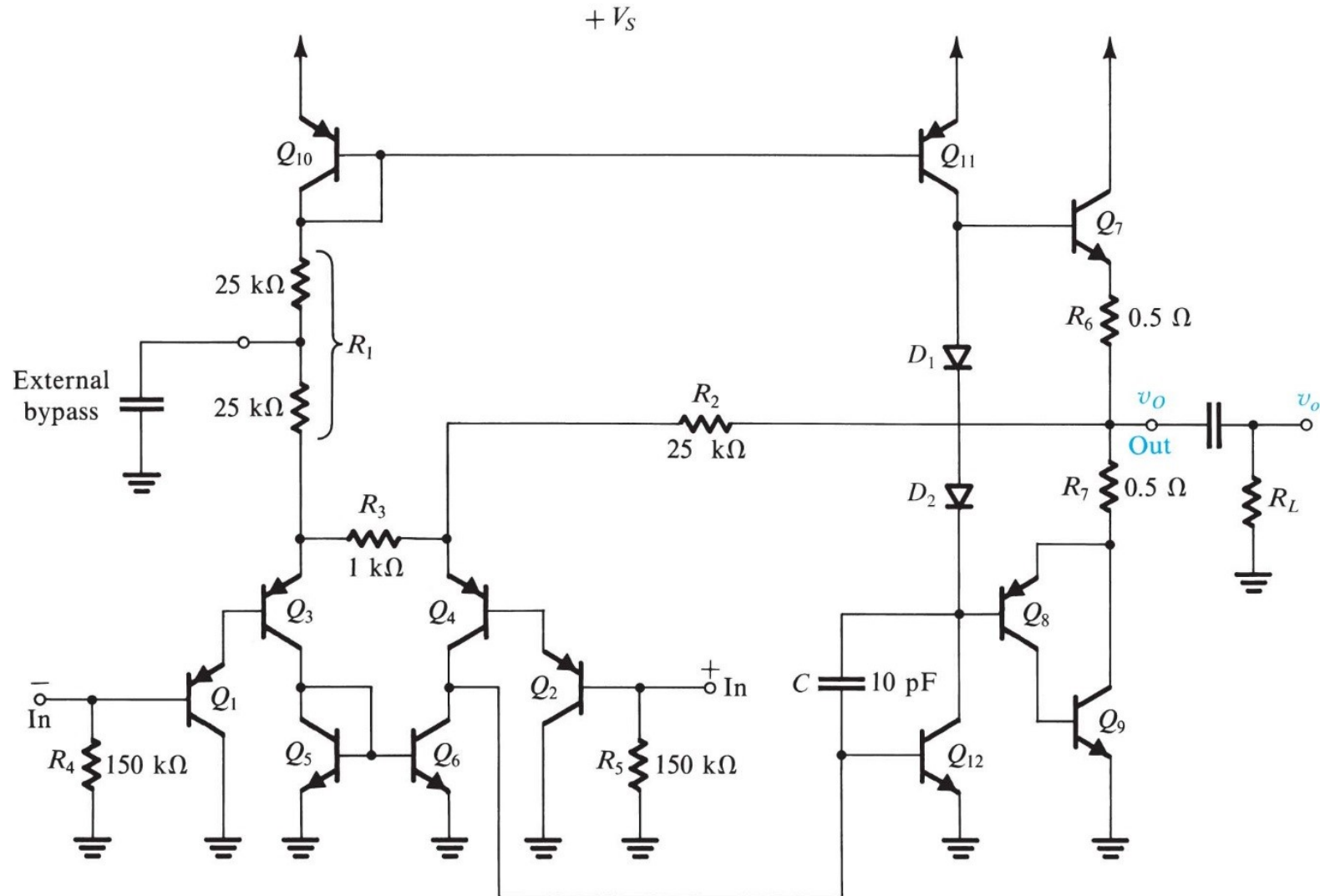


Power dissipation is high when there is current and voltage simultaneously.

Is it possible to build power amplifiers (PAs) from “normal” transistors?



Think, think, think.



(Power Transistors)

- High current requires large device: low frequency bandwidth
- High thermal dissipation: temperature coefficients and heat sinks
- High electric fields: velocity saturation

